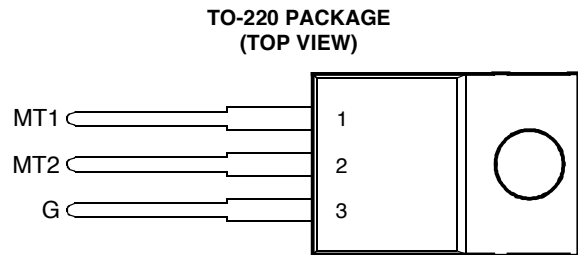




THE DATASHEET OF TIC226D-S



- 8 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 50 mA (Quadrants 1 - 3)



This series is currently available, but not recommended for new designs.



Pin 2 is in electrical contact with the mounting base.

MDC2ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC226D	V_{DRM}	400	V
	TIC226M		600	
	TIC226S		700	
	TIC226N		800	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	8	A
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)		I_{TSM}	70	A
Peak gate current		I_{GM}	±1	A
Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 μs)		P_{GM}	2.2	W
Average gate power dissipation at (or below) 85°C case temperature (see Note 4)		$P_{G(AV)}$	0.9	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 320 mA/°C.
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 4. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM} Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$			±2	mA
I_{GT} Gate trigger current	$V_{supply} = +12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		6	50	mA
	$V_{supply} = +12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-12	-50	
	$V_{supply} = -12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-10	-50	
	$V_{supply} = -12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		25		
V_{GT} Gate trigger voltage	$V_{supply} = +12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.7	2	V
	$V_{supply} = +12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.8	-2	
	$V_{supply} = -12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.8	-2	
	$V_{supply} = -12\text{ V}†$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.9	2	
V_T On-state voltage	$I_T = \pm 12\text{ A}$	$I_G = 50\text{ mA}$	(see Note 5)		±1.5	±2.1	V

† All voltages are with respect to Main Terminal 1.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_H Holding current	$V_{supply} = +12 V \dagger$ $V_{supply} = -12 V \dagger$	$I_G = 0$ $I_G = 0$	Init' $I_{TM} = 100 mA$ Init' $I_{TM} = -100 mA$		10 -6	30 -30	mA
I_L Latching current	$V_{supply} = +12 V \dagger$ $V_{supply} = -12 V \dagger$	(see Note 6)				50 -50	mA
dv/dt Critical rate of rise of off-state voltage	$V_{DRM} = \text{Rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ C$		± 100		V/ μs
dv/dt _(c) Critical rise of commutation voltage	$V_{DRM} = \text{Rated } V_{DRM}$	$I_{TRM} = \pm 12 A$	$T_C = 85^\circ C$ (see figure 7)	± 5			V/ μs

† All voltages are with respect to Main Terminal 1.

NOTES: 5. This parameter must be measured using pulse techniques, $t_p \leq 1 ms$, duty cycle $\leq 2 \%$. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

6. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics:
 $R_G = 100 \Omega$, $t_{p(g)} = 20 \mu s$, $t_r \leq 15 ns$, $f = 1 kHz$.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.8	$^\circ C/W$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ C/W$

TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT
vs**

CASE TEMPERATURE

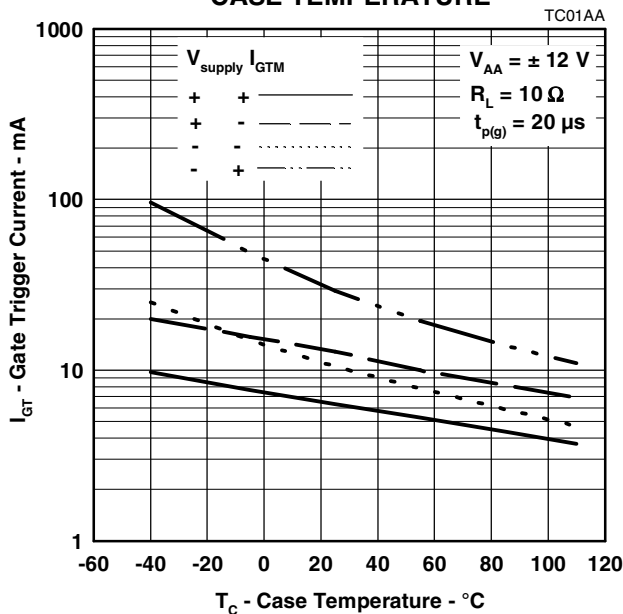


Figure 1.

**GATE TRIGGER VOLTAGE
vs**

CASE TEMPERATURE

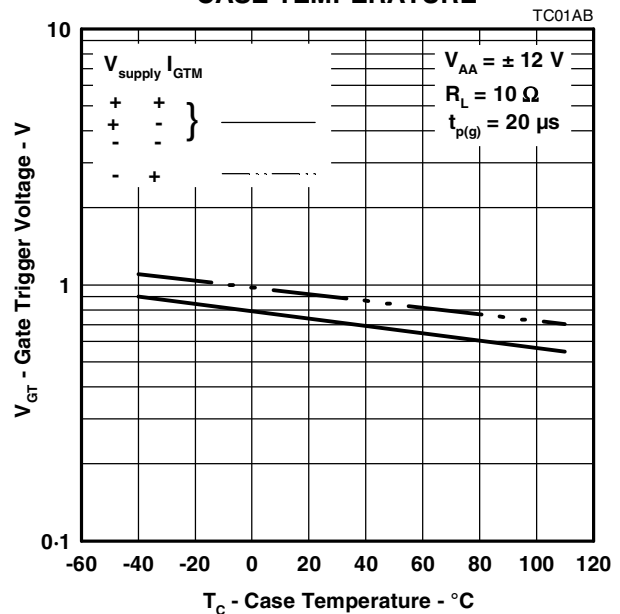
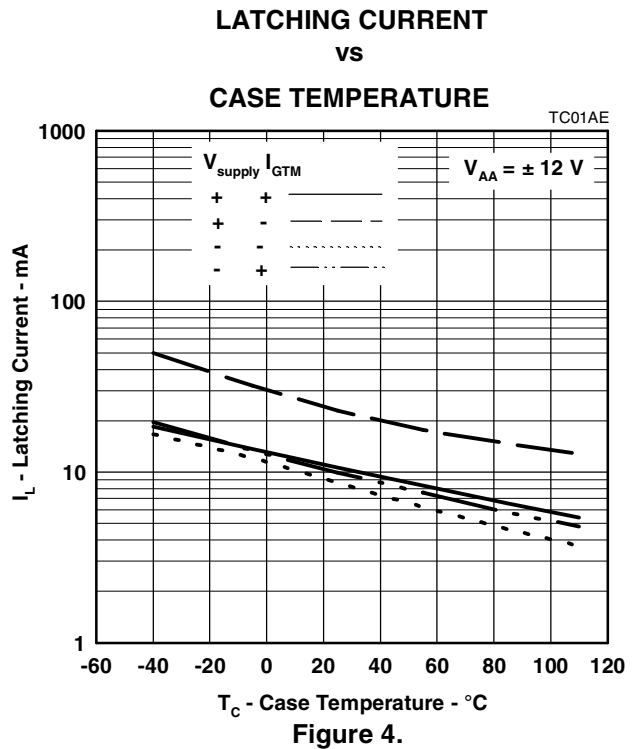
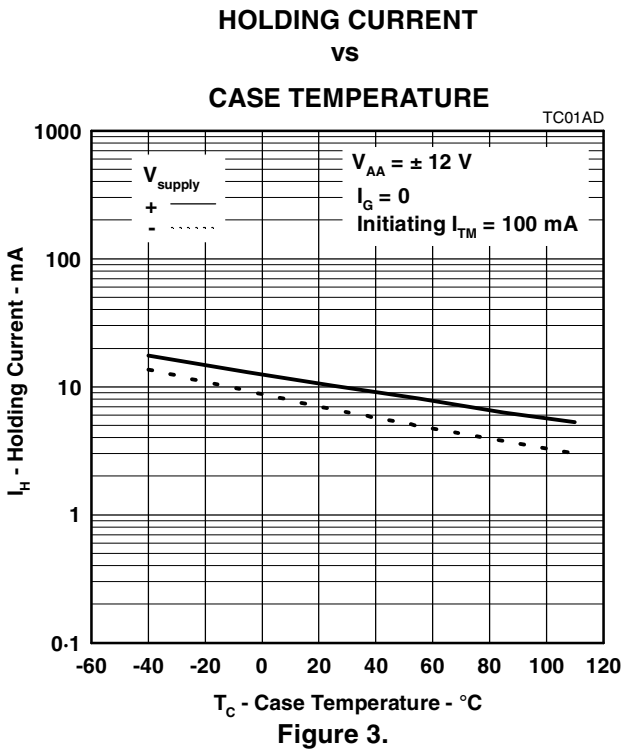


Figure 2.

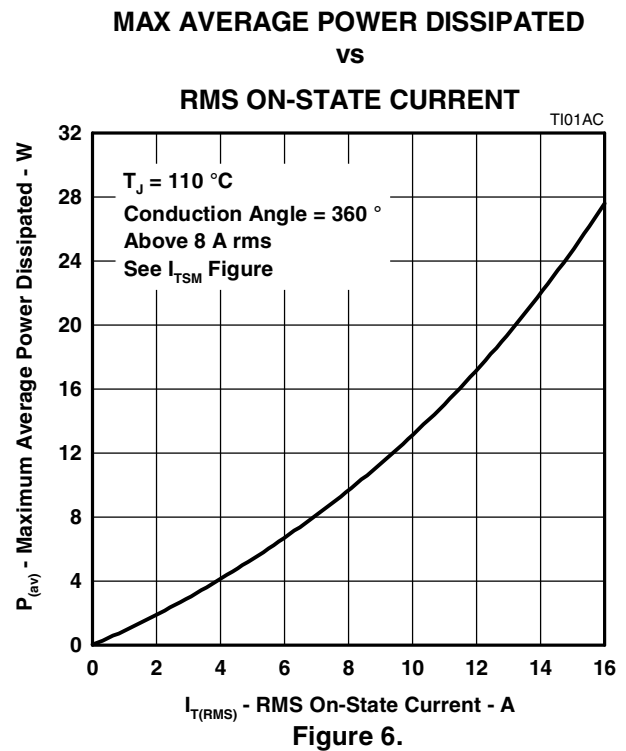
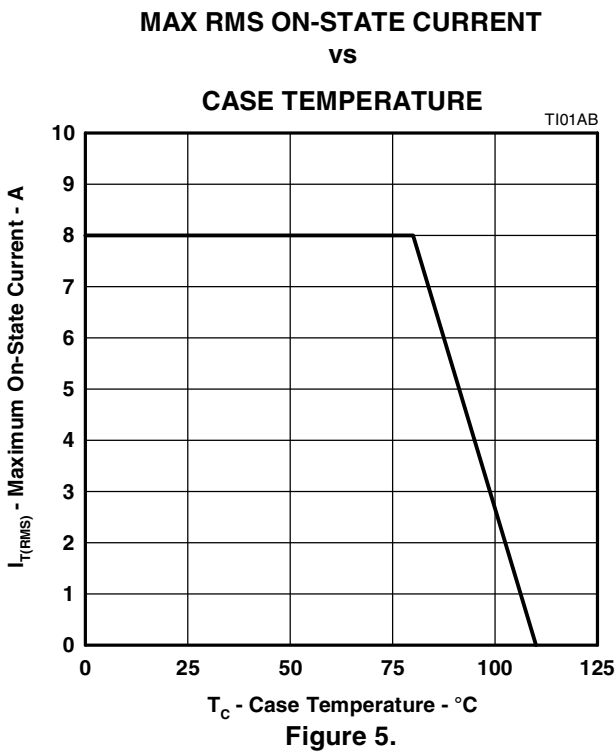
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TYPICAL CHARACTERISTICS



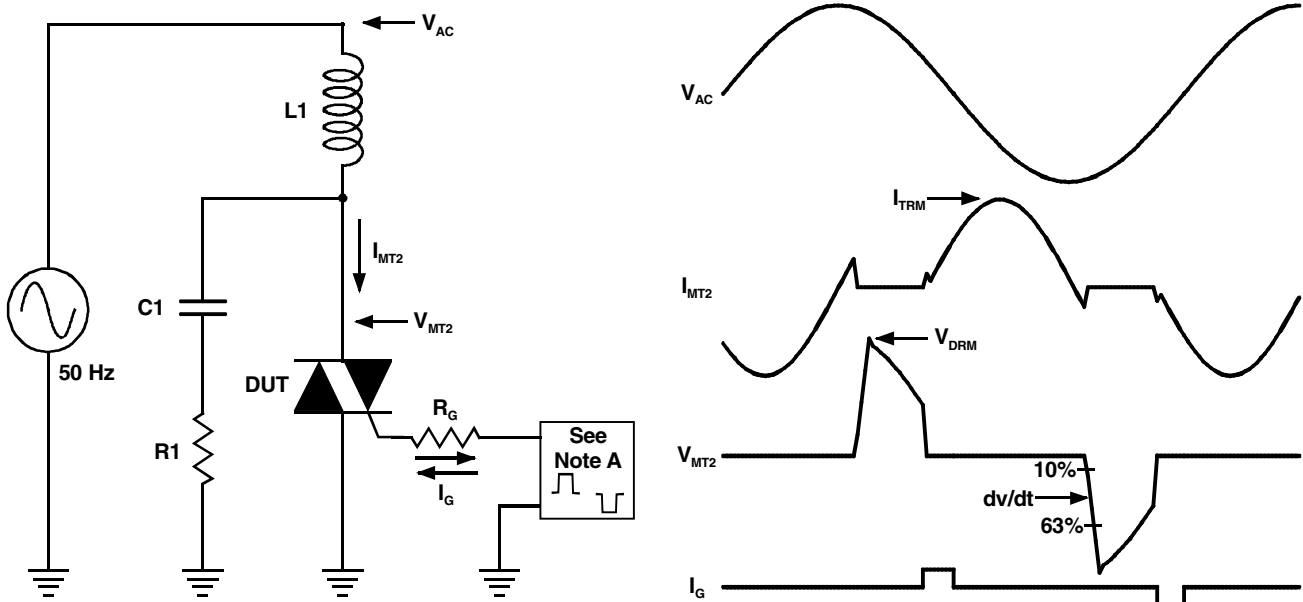
THERMAL INFORMATION



PRODUCT INFORMATION

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PARAMETER MEASUREMENT INFORMATION



NOTE A: The gate-current pulse is furnished by a trigger circuit which presents essentially an open circuit between pulses. The pulse is timed so that the off-state-voltage duration is approximately 800 μ s.

PMC2AA

Figure 7.

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